



Attorney's Docket No.: 10559-587001  
Intel Docket No.: P12768

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Been-Yih Jin et al.                      Art Unit : 2812  
Serial No. : 10/081,992                              Examiner : Ron Everett Pompey  
Filed : February 21, 2002                              Assignee : Intel Corporation  
Title : NON-SILICON SEMICONDUCTOR AND HIGH-K GATE DIELECTRIC  
METAL OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS

Mail Stop AF  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

AMENDMENT IN REPLY TO FINAL ACTION OF MAY 19, 2004

Please amend the above-identified application as follows:

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Date of Deposit

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8/18/04

*[Handwritten Signature]*

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